

ON Semiconductor

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NSS40400CF8T1G

40 V, 7 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-40	Vdc
Collector-Base Voltage	V_{CBO}	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-4.0	Adc
Collector Current – Peak	I_{CM}	-7.0	A
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	650 5.2	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	192	$^\circ\text{C}/\text{W}$
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	1.57 12.7	W mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	79	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Lead #1	$R_{\theta JL}$	15	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 sec)	$P_{D\text{single}}$ (Notes 2 & 3)	2.75	W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

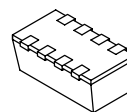
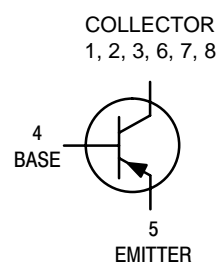
1. FR-4 @ 100 mm², 2 oz copper traces.
2. FR-4 @ 500 mm², 2 oz copper traces.
3. Thermal response.



ON Semiconductor®

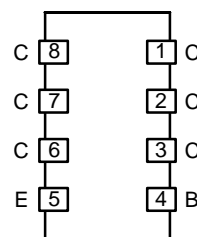
<http://onsemi.com>

**40 VOLTS
7.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 78 m Ω**

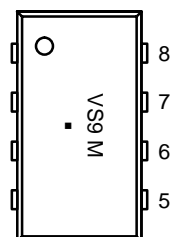


ChipFET™
CASE 1206A
STYLE 4

PIN CONNECTIONS



MARKING DIAGRAM



VS9 = Specific Device Code
M = Month Code
■ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSS40400CF8T1G	ChipFET (Pb-Free)	3000/ Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSS40400CF8T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

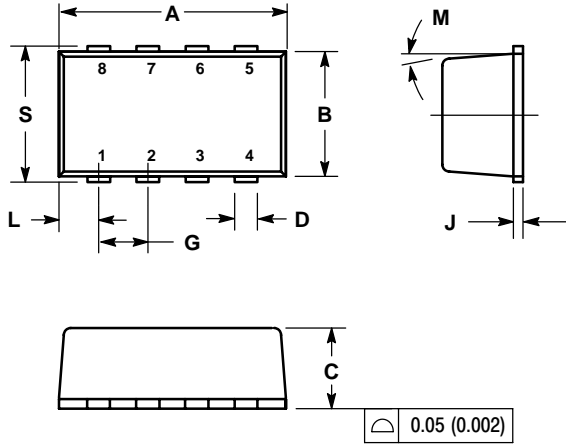
Characteristic	Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-40		–	Vdc
Collector – Base Breakdown Voltage (I _C = -0.1 mAdc, I _E = 0)	V _{(BR)CBO}	-60	–	–	Vdc
Emitter – Base Breakdown Voltage (I _E = -0.1 mAdc, I _C = 0)	V _{(BR)EBO}	-5.0	–	–	Vdc
Collector Cutoff Current (V _{CB} = -60 Vdc, I _E = 0)	I _{CBO}	–	–	-0.1	μAdc
Emitter Cutoff Current (V _{EB} = -6.0 Vdc)	I _{EBO}	–	–	-0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I _C = -1.0 A, V _{CE} = -2.0 V) (I _C = -1.5 A, V _{CE} = -2.0 V) (I _C = -2.0 A, V _{CE} = -2.0 V) (I _C = -3.0 A, V _{CE} = -2.0 V)	h _{FE}	100 100 100 100	220 220 220 220	– 400 – –	
Collector – Emitter Saturation Voltage (Note 4) (I _C = -0.1 A, I _B = -0.010 A) (I _C = -1.0 A, I _B = -0.010 A) (I _C = -2.0 A, I _B = -0.02 A) (I _C = -3.0 A, I _B = -0.030 A) (I _C = -4.0 A, I _B = -0.400 A)	V _{CE(sat)}	– – – – –	-0.010 -0.127 -0.240 -0.250 -0.180	-0.015 -0.145 -0.30 -0.45 -0.35	V
Base – Emitter Saturation Voltage (Note 4) (I _C = -1.0 A, I _B = -0.01 A)	V _{BE(sat)}	–	-0.82	-0.85	V
Base – Emitter Turn-on Voltage (Note 4) (I _C = -2.0 A, V _{CE} = -3.0 V)	V _{BE(on)}	–	-0.82	-0.875	V
Cutoff Frequency (I _C = -100 mA, V _{CE} = -5.0 V, f = 100 MHz)	f _T	100	–	–	MHz
Input Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz)	C _{ibo}	–		650	pF
Output Capacitance (V _{CB} = -3.0 V, f = 1.0 MHz)	C _{obo}	–		100	pF

4. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

NSS40400CF8T1G

PACKAGE DIMENSIONS

ChipFET
CASE 1206A-03
ISSUE F



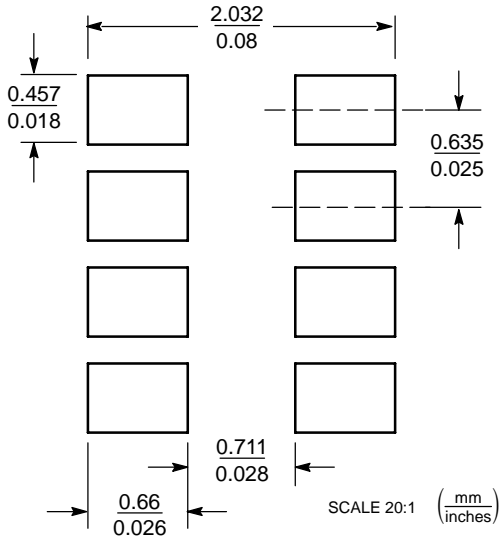
STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. COLLECTOR
4. BASE
5. EMITTER
6. COLLECTOR
7. COLLECTOR
8. COLLECTOR

NOTES:

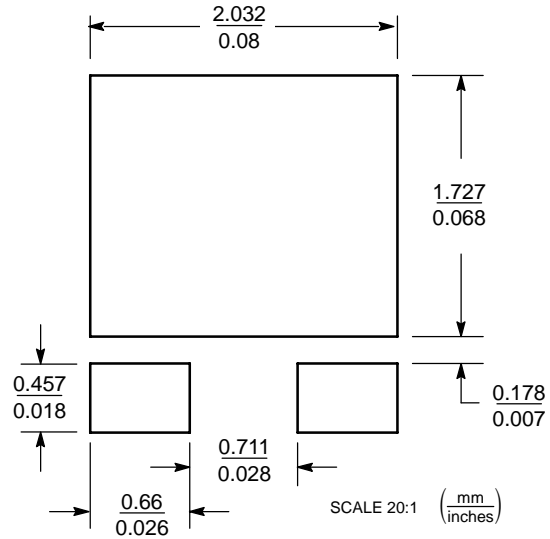
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5° NOM		5° NOM	
S	1.80	2.00	0.072	0.080

SOLDERING FOOTPRINT*




Basic



Style 4

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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